

Vertical Emission Laser Chip

VL13000010



Feature

- High power and efficiency
- Cathode bond pad on bottom side.
- Operation temperature -40~85°C

Device Electro-Optical Characteristics

All parameters for T = 25°C unless otherwise noted.

PARAMETER	SYMBOL	UNIT	MIN.	TYP.	MAX.	TEST CONDITIONS
Output power	P	mW	150			I = 200mA
Operating Voltage	Vf	Volt	1.4		1.9	I = 200mA
Wavelength	λ	nm	1270		1360	I = 200mA

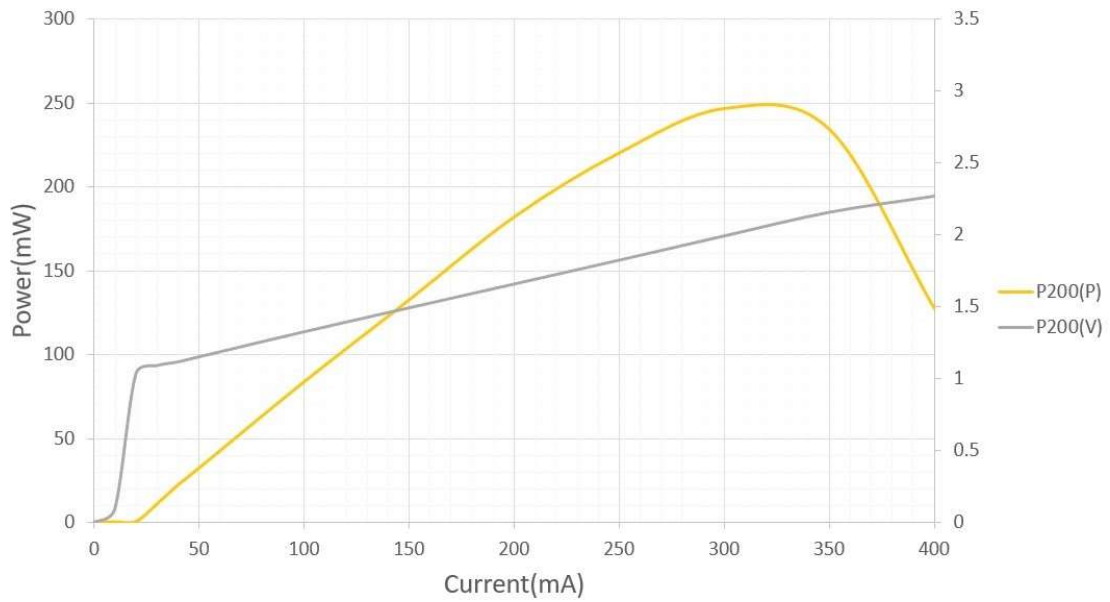
Device Physical Specifications Single Chip

PARAMETER	UNIT	MIN.	TYP.	MAX.
Bond Pad	um	95*80	100*85	105*90
Chip size	um	340X175	355X190	365X205
Chip Hight	um	135	150	165

Absolute Maximum Ratings

PARAMETER	SYMBOL	UNIT	Ratings
Forward Current	I	mA	250
Reverse Voltage	Vr	Volt	1
Operating Temperature	T _o	°C	-40 to +85
Storage Temperature (Chip on Tape)	T _{st}	°C	5 to +35
Soldering Temperature	T _{so}	°C	260 @10sec

Typical LIV Curve



Order Information

VL13000010-A01: Vertical Emission Laser Chip